



4 INCH SEMI-INSULATING SIC Substrate Specification

Grade	Zero MPD Production Grade (Z Grade)	Dummy Grade (D Grade)
Diameter	99.5 mm ~ 100.0 mm	99.5 mm ~ 100.0 mm
Poly-type	4H	4H
Thickness	500 μm \pm 15 μm	500 μm \pm 25 μm
Wafer Orientation	On axis : $\langle 0001 \rangle \pm 0.5^\circ$	On axis : $\langle 0001 \rangle \pm 0.5^\circ$
Micropipe	$\leq 1 \text{ cm}^2$	$\leq 15 \text{ cm}^2$
Resistivity	$\geq 1\text{E}10 \ \Omega\text{-cm}$	$\geq 1 \text{E}5 \ \Omega\text{-cm}$
Primary Flat Orientation	$\{10\text{-}10\} \pm 5.0^\circ$	$\{10\text{-}10\} \pm 5.0^\circ$
Primary Flat Length	32.5 mm \pm 2.0 mm	32.5 mm \pm 2.0 mm
Secondary Flat Length	18.0 mm \pm 2.0 mm	18.0 mm \pm 2.0 mm
Secondary Flat Orientation	Silicon face up: 90° CW. from Prime flat $\pm 5.0^\circ$	Silicon face up: 90° CW. from Prime flat $\pm 5.0^\circ$
Edge Exclusion	3 mm	3 mm
LTV / TTV / Bow / Warp	$\leq 2.5 \ \mu\text{m} / \leq 5 \ \mu\text{m} / \leq 15 \ \mu\text{m} / \leq 30 \ \mu\text{m}$	$\leq 10 \ \mu\text{m} / \leq 15 \ \mu\text{m} / \leq 25 \ \mu\text{m} / \leq 40 \ \mu\text{m}$
Roughness	Polish Ra $\leq 1 \text{ nm}$	Polish Ra $\leq 1 \text{ nm}$
	CMP Ra $\leq 0.2 \text{ nm}$	CMP Ra $\leq 0.2 \text{ nm}$
Edge Cracks By High Intensity Light	—	Cumulative length $\leq 10 \text{ mm}$ single length $\leq 2 \text{ mm}$
Hex Plates By High Intensity Light	Cumulative area $\leq 0.05\%$	Cumulative area $\leq 0.1\%$
Polytype Areas By High Intensity Light	—	Cumulative area $\leq 3\%$
Visual Carbon Inclusions	Cumulative area $\leq 0.05\%$	Cumulative area $\leq 3\%$
Silicon Surface Scratches By High Intensity Light	—	Cumulative length $\leq 1 \times$ wafer diameter
Edge Chips High By Intensity Light	None permitted $\geq 0.2 \text{ mm}$ width and depth	5 allowed, $\leq 1 \text{ mm}$ each
Silicon Surface Contamination By High Intensity	—	—
Packaging	Multi-wafer Cassette Or Single Wafer Container	Multi-wafer Cassette Or Single Wafer Container